BYQ28X-200

Dual ultrafast rugged rectifier diode

Rev. 03 — 18 July 2018

Product data sheet

1. Product profile

1.1 General description

Dual ultrafast epitaxial rectifier diodes in a SOT186A (TO-220F) isolated plastic package.

1.2 Features and benefits

- Fast switching
- Guaranteed ESD capability
- High thermal cycling performance
- Low on-state losses
- Soft recovery minimizes power-consuming oscillations

1.3 Applications

 Output rectifiers in high-frequency switched-mode power supplies

1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
V_{RRM}	repetitive peak reverse voltage		-	-	200	V	
I _{O(AV)}	average output current	SQW; δ = 0.5; T _h ≤ 92 °C; both diodes conducting; see Figure 1; see Figure 2	-	-	10	Α	
I _{FRM}	repetitive peak forward current	SQW; δ = 0.5; t_p = 25 μ s; $T_h \le$ 92 °C; per diode	-	-	10	Α	
Dynamic characteristics							
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; ramp recovery; see Figure 5	-	15	25	ns	
Static ch	aracteristics						
V _F	forward voltage	$I_F = 5 \text{ A}; T_j = 150 \text{ °C}; \text{ see}$ Figure 4	-	8.0	0.895	V	
Electros	Electrostatic discharge						
V _{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 k Ω ; all pins	-	-	8	kV	

Dual ultrafast rugged rectifier diode

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	K	cathode	mb	A1 + + A2
3	A2	anode 2		K
mb	n.c.	mounting base; isolated		sym125
			SOT186A	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYQ28X-200	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

(TO-220F)

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	200	V
V_{RWM}	crest working reverse voltage		-	200	V
V_R	reverse voltage	DC	-	200	V
$I_{O(AV)}$	average output current	SQW; δ = 0.5; T _h ≤ 92 °C; both diodes conducting; see Figure 1; see Figure 2	-	10	Α
I _{FRM}	repetitive peak forward current	SQW; $\bar{\delta}$ = 0.5; t_p = 25 μ s; $T_h \le$ 92 °C; per diode	-	10	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; SIN; $T_{j(init)}$ = 25 °C; per diode	-	50	Α
		t_p = 8.3 ms; SIN; $T_{j(init)}$ = 25 °C; per diode	-	55	Α
I _{RRM}	repetitive peak reverse current	$t_p = 2 \ \mu s; \ \delta = 0.001$	-	0.2	Α
I _{RSM}	non-repetitive peak reverse current	$t_p = 100 \ \mu s$	-	0.2	А
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C
Electrostatic discharge					
V_{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 k Ω ; all pins	-	8	kV

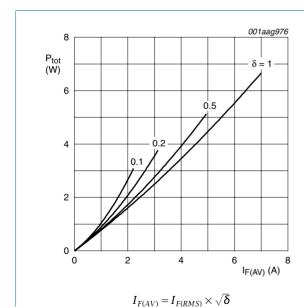


Fig 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

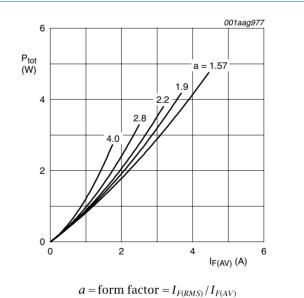


Fig 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

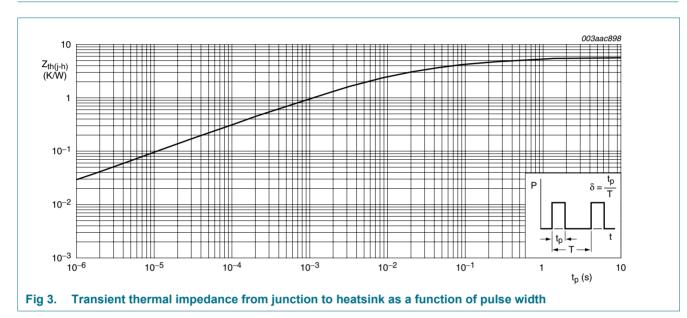
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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; see Figure 3	-	-	5.7	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air		-	55	-	K/W



6. Isolation characteristics

Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	50 Hz < f < 60 Hz; sinusoidal waveform; relative humidity < 65 %; clean and dust free; from all terminals to external heatsink	-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink; f = 1 MHz	-	10	-	pF

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7. Characteristics

Table 7. Characteristics

Parameter	Conditions	Min	Тур	Max	Unit
racteristics					
forward voltage	I _F = 10 A; T _j = 25 °C	-	1.1	1.25	V
	$I_F = 5 \text{ A}$; $T_j = 150 \text{ °C}$; see Figure 4	-	0.8	0.895	V
	I _F = 5 A; T _j = 25 °C	-	0.95	1.1	V
reverse current	V _R = 200 V; T _j = 25 °C	-	2	10	μΑ
	V _R = 200 V; T _j = 100 °C	-	0.1	0.2	mΑ
characteristics					
recovered charge	$I_F = 2 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 20 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$	-	4	9	μC
reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; ramp recovery; $T_j = 25 \text{ °C}$; see Figure 5	-	15	25	ns
	I_F = 0.5 A; I_R = 1 A; step recovery; measured at I_R = 0.25 A; T_j = 25 °C; see Figure 6	-	-	20	ns
peak reverse recovery current	$I_F = 5 \text{ A}$; $V_R \ge 30 \text{ V}$; $dI_F/dt = 50 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 5	-	0.5	0.7	Α
peak forward recovery voltage	$I_F = 1 \text{ A}$; $dI_F/dt = 10 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 7	-	1	-	V
	reverse current characteristics recovered charge reverse recovery time peak reverse recovery current peak forward recovery	forward voltage $I_{F} = 10 \text{ A; } T_{j} = 25 \text{ °C}$ $I_{F} = 5 \text{ A; } T_{j} = 150 \text{ °C; see } \underline{\text{Figure 4}}$ $I_{F} = 5 \text{ A; } T_{j} = 25 \text{ °C}$ $V_{R} = 200 \text{ V; } T_{j} = 25 \text{ °C}$ $V_{R} = 200 \text{ V; } T_{j} = 100 \text{ °C}$ $Characteristics$ $\text{recovered charge} \qquad I_{F} = 2 \text{ A; } V_{R} = 30 \text{ V; dI}_{F}/\text{dt} = 20 \text{ A/\mu s; }$ $T_{j} = 25 \text{ °C}$ $\text{reverse recovery time} \qquad I_{F} = 1 \text{ A; } V_{R} = 30 \text{ V; dI}_{F}/\text{dt} = 100 \text{ A/\mu s; }$ $\text{ramp recovery; } T_{j} = 25 \text{ °C; see } \underline{\text{Figure 5}}$ $I_{F} = 0.5 \text{ A; } I_{R} = 1 \text{ A; step recovery; }$ $\text{measured at } I_{R} = 0.25 \text{ A; } T_{j} = 25 \text{ °C; see }$ $\underline{\text{Figure 6}}$ $\text{peak reverse recovery current} \qquad I_{F} = 5 \text{ A; } V_{R} \geq 30 \text{ V; dI}_{F}/\text{dt} = 50 \text{ A/\mu s; }$ $T_{j} = 25 \text{ °C; see } \underline{\text{Figure 5}}$ $\text{peak forward recovery} \qquad I_{F} = 1 \text{ A; dI}_{F}/\text{dt} = 10 \text{ A/\mu s; } T_{j} = 25 \text{ °C; see}$	$ \begin{array}{lll} & & & & & & \\ & & & & & \\ & & & & \\ & & & & \\ & & & \\ & & & \\ & & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & \\ & & \\ & $	$ \begin{array}{c} \text{racteristics} \\ \text{forward voltage} & I_F = 10 \text{ A; } T_j = 25 \text{ °C} & - & 1.1 \\ I_F = 5 \text{ A; } T_j = 150 \text{ °C; see } \underline{\text{Figure 4}} & - & 0.8 \\ I_F = 5 \text{ A; } T_j = 25 \text{ °C} & - & 0.95 \\ \text{reverse current} & V_R = 200 \text{ V; } T_j = 25 \text{ °C} & - & 2 \\ \hline V_R = 200 \text{ V; } T_j = 100 \text{ °C} & - & 0.1 \\ \text{characteristics} \\ \text{recovered charge} & I_F = 2 \text{ A; } V_R = 30 \text{ V; } dI_F/dt = 20 \text{ A/\mu s; } & - & 4 \\ \hline T_j = 25 \text{ °C} & - & 15 \\ \hline \text{reverse recovery time} & I_F = 1 \text{ A; } V_R = 30 \text{ V; } dI_F/dt = 100 \text{ A/\mu s; } & - & 15 \\ \hline I_F = 0.5 \text{ A; } I_R = 1 \text{ A; step recovery; } & - & - \\ \hline \text{measured at } I_R = 0.25 \text{ A; } T_j = 25 \text{ °C; see } \\ \hline \text{Figure 6} & - & 0.5 \\ \hline \text{peak reverse recovery} & I_F = 5 \text{ A; } V_R \geq 30 \text{ V; } dI_F/dt = 50 \text{ A/\mu s; } & - & 0.5 \\ \hline \text{peak forward recovery} & I_F = 1 \text{ A; } dI_F/dt = 10 \text{ A/\mu s; } T_j = 25 \text{ °C; see} & - & 1 \\ \hline \end{array}$	$ \begin{array}{c} \text{racteristics} \\ \text{forward voltage} \\ & \begin{array}{c} I_F = 10 \text{ A}; \ T_j = 25 \text{ °C} \\ \hline I_F = 5 \text{ A}; \ T_j = 150 \text{ °C}; \text{ see } \underline{\text{Figure 4}} \\ \hline I_F = 5 \text{ A}; \ T_j = 25 \text{ °C} \\ \hline I_F = 5 \text{ A}; \ T_j = 25 \text{ °C} \\ \hline I_F = 200 \text{ V}; \ T_j = 25 \text{ °C} \\ \hline V_R = 200 \text{ V}; \ T_j = 100 \text{ °C} \\ \hline V_R = 200 \text{ V}; \ T_j = 100 \text{ °C} \\ \hline \end{array} \qquad \begin{array}{c} - 2 & 10 \\ \hline 0.1 & 0.2 \\ \hline \end{array} $

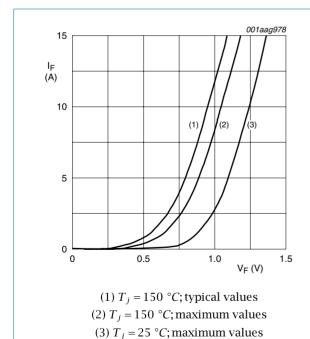


Fig 4. Forward current as a function of forward

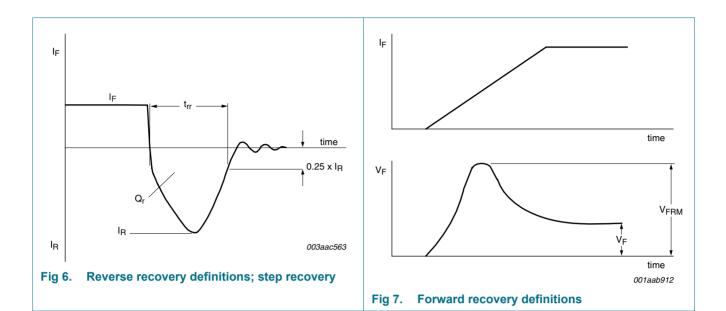
 $I_{\rm R}$ $\frac{{\rm d}I_{\rm F}}{{\rm d}t}$ $\frac{{\rm d}I_{\rm F}}{{\rm d}t}$ $\frac{{\rm time}}{{\rm l}_{\rm RM}}$ $\frac{{\rm time}}{{\rm l}_{\rm RM}}$

Fig 5. Reverse recovery definitions; ramp recovery

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voltage

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8. Package outline

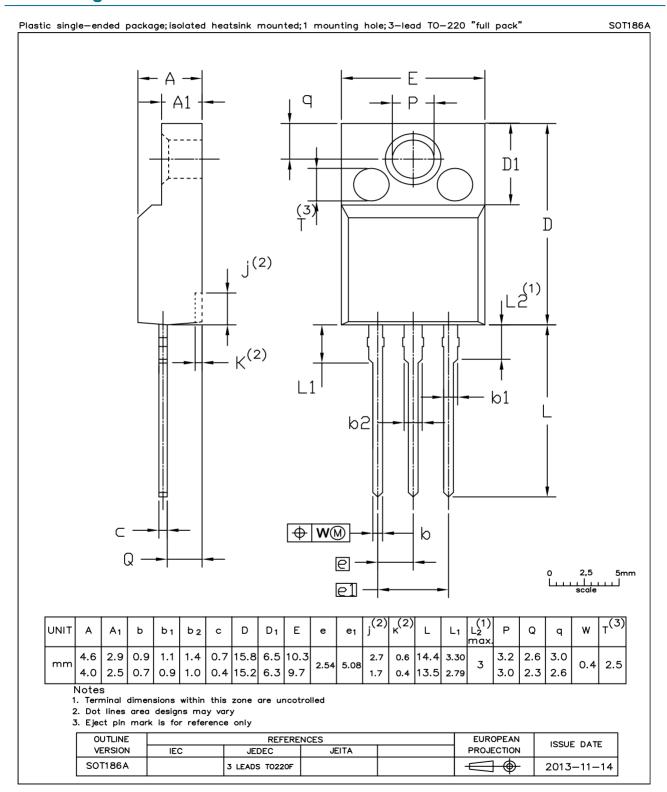


Fig. 8. Package outline TO-220F (SOT186A)



Dual ultrafast rugged rectifier diode

Revision history

Table 8. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYQ28X-200_3	20180718	Product data sheet	-	BYQ28X-200_2
Modifications:	Change N.	XP logo to WeEn logo.		
	 Update P0 	DD to combine different as	ssembly plant.	
BYQ28X-200_2	20090205	Product data sheet	-	BYQ28X_SERIES_1
Modifications: • The format of this data sheet has been redesigned to comply with the new id guidelines of NXP Semiconductors.				
	 Legal texts 	have been adapted to th	e new company name w	here appropriate.
	 Type numb 	oer BYQ28X-200 separate	ed from data sheet BYQ	28X_SERIES_1.
BYQ28X_SERIES_1	19960801	Product data sheet	-	-

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10. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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Dual ultrafast power diode

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